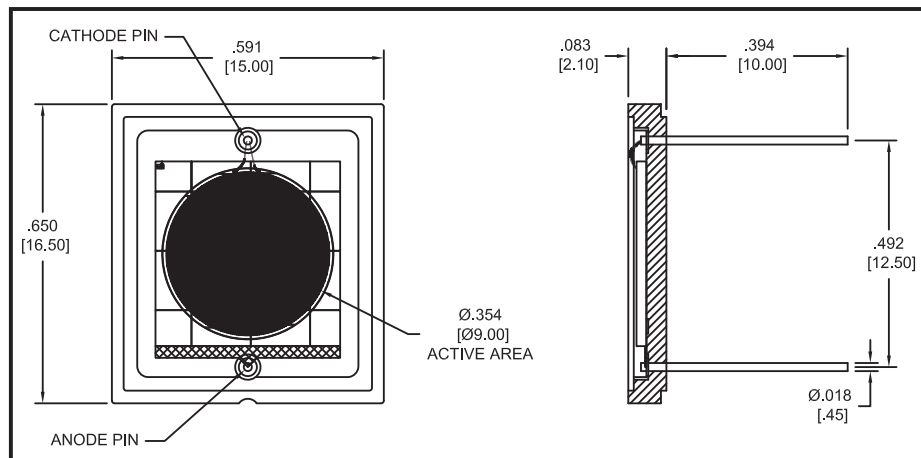


**FEATURES**

- Circular active area
- Ideal for electron detection
- 100% internal QE
- High speed

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	9mm		63		mm ²
Responsivity, $\mathcal{R}$	(see graphs on next page)				A/W
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$	160			Volts
Capacitance, C	$V_R = 0V$			10	pF
Rise Time	$RL = 50\Omega$, $V_R = 2V$			2	nsec
Dark Current	$V_R = 150V$			100	nA

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient ¹	-10° TO 40°C ¹
Nitrogen or Vacuum	-20°C TO 80°C
Maximum Junction Temperature	70°C
Lead soldering temperature ²	260°C

¹Temperatures exceeding these parameters may create oxide growth on the active area.

Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

²0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.

Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

